# CGD987HCI

# 1 GHz, 27 dB gain GaAs high output power doubler Rev. 1 — 29 June 2011 Produc

Product data sheet

#### 1. **Product profile**

### 1.1 General description

Hybrid amplifier module in a SOT115J package, operating at a supply voltage of 24 V Direct Current (DC), employing Hetero junction Field Effect Transistor (HFET) GaAs dies.

### 1.2 Features and benefits

- Excellent linearity
- Optimized for flat PAL D and flat NTSC loading
- Superior levels of ESD protection
- Extremely low noise
- Excellent return loss properties
- Gain compensation over temperature
- Rugged construction
- Unconditionally stable
- Thermally optimized design
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)
- Integrated ring wave surge protection

### 1.3 Applications

CATV systems operating in the 40 MHz to 862 MHz / 1003 MHz frequency range using PAL D or NTSC channel conditions.

### 1.4 Quick reference data

Quick reference data

Bandwidth 40 MHz to 1003 MHz;  $V_B = 24 \text{ V (DC)}$ ;  $Z_S = Z_L = 75 \Omega$ ;  $T_{mb} = 35 \text{ °C}$ ; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz		-	25.5	-	dB
		f = 1003 MHz		26	27	28	dB
СТВ	composite triple beat	V <sub>o</sub> = 48 dBmV at 862 MHz	[1]	-	-66	-62	dBc
CSO	composite second-order distortion	$V_0 = 48 \text{ dBmV at } 862 \text{ MHz}$	[1]	-	-66	-60	dBc
I <sub>tot</sub>	total current		[2]	-	440	460	mA

<sup>[1] 98</sup> PAL D channels with 8 MHz bandwidth per channel; [f = 47 MHz to 862 MHz]; flat  $V_0$  till 862 MHz.



<sup>[2]</sup> Direct Current (DC).

# 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline Graphic symbol
1	input	
2, 3	common	1 3 5 7 9
5	+V <sub>B</sub>	
7, 8	common	12,3,7,8
9	output	sym095

# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
CGD987HCI	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J			

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Mi	n Max	Unit
$V_B$	supply voltage		-	30	V
$V_{i(RF)}$	RF input voltage	single tone	-	75	dBmV
V <sub>ESD</sub>	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E	[1] -	2000	V
		Biased; According IEC61000-4-2	-	1500	V
T <sub>stg</sub>	storage temperature		-4	0 +100	°C
T <sub>mb</sub>	mounting base temperature		-2	0 +100	°C

<sup>[1]</sup> The ESD pulse of 2000 V corresponds to a class 2 sensitivity level.

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## 5. Characteristics

Table 5. Characteristics

Bandwidth 40 MHz to 1003 MHz;  $V_B = 24 \text{ V (DC)}$ ;  $Z_S = Z_L = 75 \Omega$ ;  $T_{mb} = 35 \text{ °C}$ ; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz		-	25.5	-	dB
		f = 870 MHz		-	26.5	-	dB
		f = 1003 MHz		26	27	28	dB
SL <sub>sl</sub>	slope straight line	f = 40 MHz to 1003 MHz	[1]	0.7	-	2.2	dB
FL	flatness of frequency response	f = 40 MHz to 1003 MHz	[2]	-	-	1	dB
RLin	input return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		19	-	-	dB
		f = 320 MHz to 640 MHz		18	-	-	dB
		f = 640 MHz to 870 MHz		17	-	-	dB
		f = 870 MHz to 1003 MHz		16	-	-	dB
$RL_out$	output return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		18	-	-	dB
		f = 320 MHz to 640 MHz		17	-	-	dB
		f = 640 MHz to 870 MHz		16	-	-	dB
		f = 870 MHz to 1003 MHz		16	-	-	dB
NF	noise figure	f = 50 MHz		-	4.5	5.5	dB
		f = 1003 MHz		-	5	6	dB
I <sub>tot</sub>	total current		[3]	-	440	460	mΑ

<sup>[1]</sup>  $G_p$  at 1003 MHz minus  $G_p$  at 40 MHz.

<sup>[2]</sup> Flatness is defined as peak deviation to straight line.

<sup>[3]</sup> Direct Current (DC).



Table 6. Distortion characteristics

Bandwidth 40 MHz to 1003 MHz;  $V_B = 24 \text{ V (DC)}$ ;  $Z_S = Z_L = 75 \Omega$ ;  $T_{mb} = 35 \text{ °C}$ ; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
98 PAL [	) channels					
СТВ	composite triple beat	V <sub>o</sub> = 48 dBmV at 862 MHz	<u>[1]</u> -	-66	-62	dBc
		V <sub>o</sub> = 50 dBmV at 862 MHz	<u>[1]</u> -	-62	-	dBc
CSO	composite second-order distortion	V <sub>o</sub> = 48 dBmV at 862 MHz	<u>[1]</u> -	-66	-60	dBc
		V <sub>o</sub> = 50 dBmV at 862 MHz	<u>[1]</u> -	-63	-	dBc
Xmod	cross modulation	V <sub>o</sub> = 48 dBmV at 862 MHz	<u>[1]</u> -	-68	-	dB
		V <sub>o</sub> = 50 dBmV at 862 MHz	<u>[1]</u> -	-60	-	dB
112 NTS	C channels					
СТВ	composite triple beat	V <sub>o</sub> = 48 dBmV at 750 MHz	[2]	-63	-	dBc
CSO	composite second-order distortion	V <sub>o</sub> = 48 dBmV at 750 MHz	[2] _	-64	-	dBc
Xmod	cross modulation	V <sub>o</sub> = 48 dBmV at 750 MHz	[2]	-66	-	dB
79 NTSC	channels + 75 digital channels					
СТВ	composite triple beat	V <sub>o</sub> = 56.4 dBmV at 1003 MHz	[3]	<b>-75</b>	-	dBc
CSO	composite second-order distortion	V <sub>o</sub> = 56.4 dBmV at 1003 MHz	[3]	-70	-	dBc
Xmod	cross modulation	V <sub>o</sub> = 56.4 dBmV at 1003 MHz	[3]	-68	-	dB
CCN	carrier-to-composite noise	V <sub>o</sub> = 56.4 dBmV at 1003 MHz	[3]	57	-	dBc

<sup>[1] 98</sup> PAL D channels with 8 MHz bandwidth per channel; [f = 47 MHz to 862 MHz]; flat  $V_0$  till 862 MHz.

<sup>[2] 112</sup> NTSC channels; [f = 45 MHz to 750 MHz]; flat  $V_0$  till 750 MHz.

<sup>[3] 79</sup> NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1003 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1003 MHz.

# 6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J

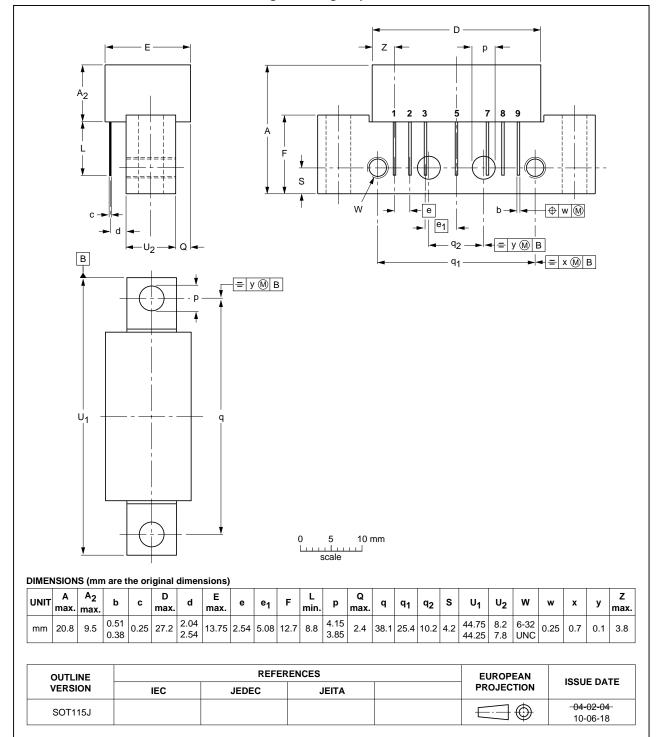


Fig 1. Package outline SOT115J

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# 7. Abbreviations

Table 7. Abbreviations

Acronym	Description
CATV	Community Antenna TeleVision
ESD	ElectroStatic Discharge
GaAs	Gallium-Arsenide
NTSC	National Television Standard Committee
PAL	Phase Alternate Line
RF	Radio Frequency
UNC	UNified Coarse

# 8. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
CGD987HCI v.1	20110629	Product data sheet	-	-

## 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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